

BCZS65N45M1

N-Channel Silicon Carbide Power MOSFET

650 V, 44 A, 45 mΩ



bestirpower

Features

- High switching speed with a low gate charge
- Fast intrinsic diode with low reverse recovery
- Robust Avalanche Capability
- 100% Avalanche Tested
- Halogen Free, and RoHS Compliant

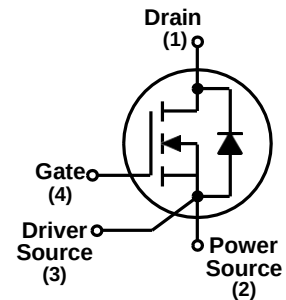
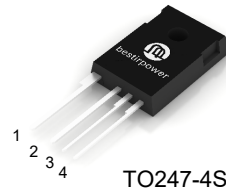
$BV_{DSS}, T_c=25^{\circ}\text{C}$	$I_D, T_c=25^{\circ}\text{C}$	$R_{DS(on),typ}$	$Q_{g,typ}$
650 V	44 A	45 mΩ	55 nC

Benefits

- System efficiency improvement
- Higher frequency applicability
- Increased power density
- Reduced cooling effort

Applications

- Solar inverter / ESS / UPS
- EV charging station
- Server & Telecom power
- Industrial power supply



Absolute Maximum Ratings ($T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain to Source Voltage		650	V
V_{GS}	Gate to Source Voltage (DC)		-10 / +22	V
V_{GSop}	Recommended Operation Value		-5 / +18	V
I_D	Drain Current	$V_{GS} = 18 \text{ V}, (T_C = 25^{\circ}\text{C})$	44	A
		$V_{GS} = 18 \text{ V}, (T_C = 100^{\circ}\text{C})$	31	
I_{DM}	Drain Current	Pulsed (Note1)	117	A
P_D	Power Dissipation	$(T_C = 25^{\circ}\text{C})$	150	W
		Derate Above 25°C	1.0	W/ $^{\circ}\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to 175	$^{\circ}\text{C}$

※Note 1 : Limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.0	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	
T_{sold}	Soldering temperature, wave soldering only allowed at leads	260	$^{\circ}\text{C}$

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	650	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$	-	1	100	μA
		$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}, T_J = 175^\circ\text{C}$	-	10	-	
I_{GSS}	Gate-Source Leakage Current	$V_{GS} = +22\text{ V}, V_{DS} = 0\text{ V}$	-	-	+100	nA
		$V_{GS} = -10\text{ V}, V_{DS} = 0\text{ V}$	-	-	-100	

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 7\text{ mA}$	1.8	2.8	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 18\text{ V}, I_D = 20\text{ A}$	-	45	63	mΩ
		$V_{GS} = 18\text{ V}, I_D = 20\text{ A}, T_J = 175^\circ\text{C}$	-	59	-	
g_{fs}	Transconductance	$V_{DS} = 20\text{ V}, I_D = 20\text{ A}$	-	13.4	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	1048	-	μF
C_{oss}	Output Capacitance		-	131	-	
C_{rss}	Reverse Capacitance		-	9.1	-	
E_{oss}	Stored Energy in Output Capacitance	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$	-	13.0	-	μJ
$C_{o(er)}$	Energy Related Output Capacitance		-	162.0	-	pF
$C_{o(tr)}$	Time Related Output Capacitance		-	236	-	
$Q_{g(tot)}$	Total Gate Charge	$V_{DS} = 400\text{ V}, I_D = 20\text{ A},$ $V_{GS} = -5\text{ V} / 18\text{ V},$ Inductive load	-	56	-	nC
Q_{gs}	Gate to Source Charge		-	14	-	
Q_{gd}	Gate to Drain "Miller" Charge		-	15	-	
R_G	Internal Gate Resistance	$f = 1\text{ MHz}, V_{AC} = 30\text{ mV}$ open drain	-	4.0	-	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 400\text{ V}, I_D = 20\text{ A},$ $V_{GS} = -5\text{ V} / 18\text{ V}, R_G = 2\text{ }\Omega,$ FWD : BCH65S012D1, Inductive load	-	13	-	ns
t_r	Turn-On Rise Time		-	10	-	
$t_{d(off)}$	Turn-Off Delay Time		-	26	-	
t_f	Turn-Off Fall Time		-	5	-	
E_{on}	Turn-on Switching Energy		-	27	-	μJ
E_{off}	Turn-off Switching Energy		-	18	-	
E_{tot}	Total Switching Energy		-	45	-	

Source-Drain Diode Characteristics

I_S	Maximum Continuous Diode Forward Current	$V_{GS} = -5\text{ V}, I_{SD} = 20\text{ A}$	-	-	42	A
I_{SM}	Maximum Pulsed Diode Forward Current		-	-	117	
V_{SD}	Diode Forward Voltage	$V_{GS} = -5\text{ V}, I_{SD} = 20\text{ A}$	-	4.2	-	V
t_{rr}	Reverse Recovery Time	$V_{DD} = 400\text{ V}, I_{SD} = 20\text{ A},$ $di_f/dt = 1000\text{ A}/\mu\text{s}$, Includes Q_{OSS}	-	17	-	ns
Q_{rr}	Reverse Recovery Charge		-	104	-	nC
I_{rrm}	Peak Reverse Recovery Current		-	10	-	A

Typical Performance Characteristics

Figure 1. On-Region Characteristics $T_J = -40^\circ\text{C}$

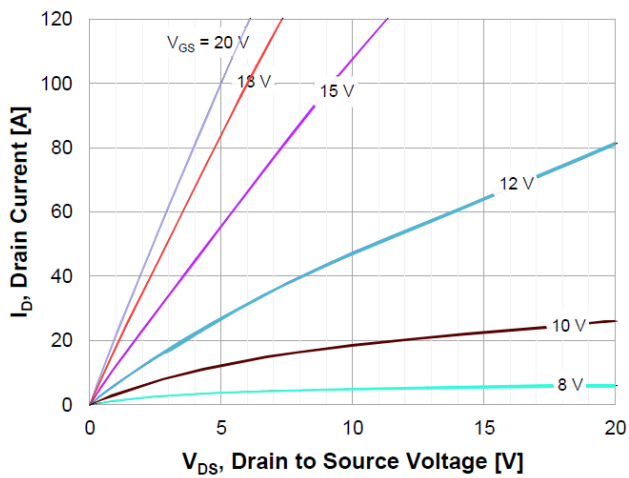


Figure 2. On-Region Characteristics $T_J = 25^\circ\text{C}$

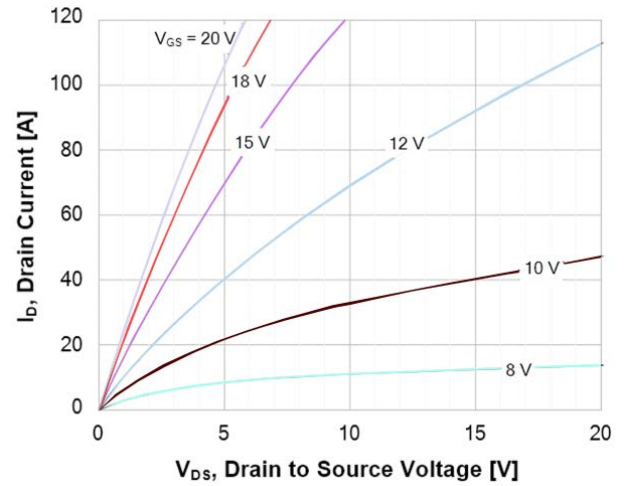


Figure 3. On-Region Characteristics $T_J = 125^\circ\text{C}$

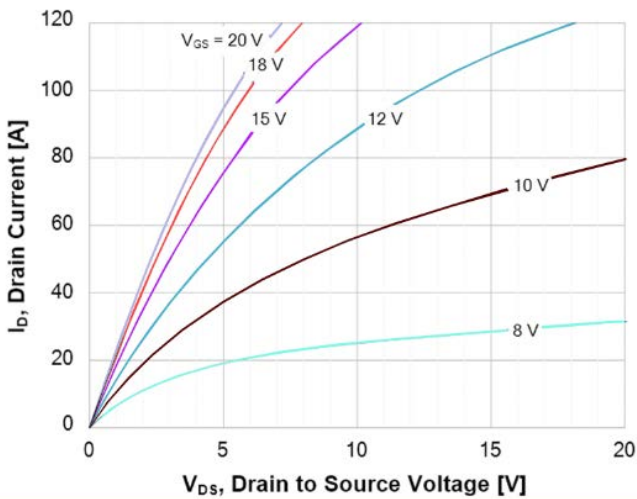


Figure 4. On-Region Characteristics $T_J = 175^\circ\text{C}$

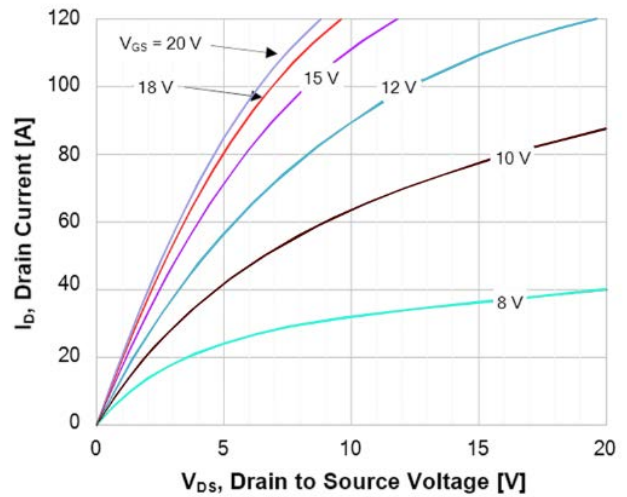


Figure 5. On-Resistance Characteristics vs. Temperature

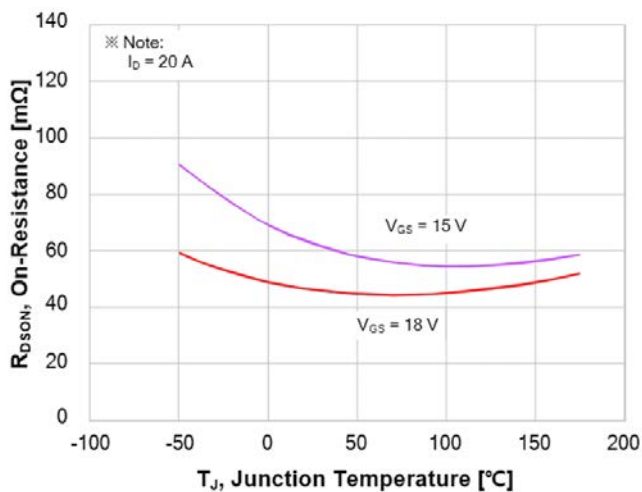
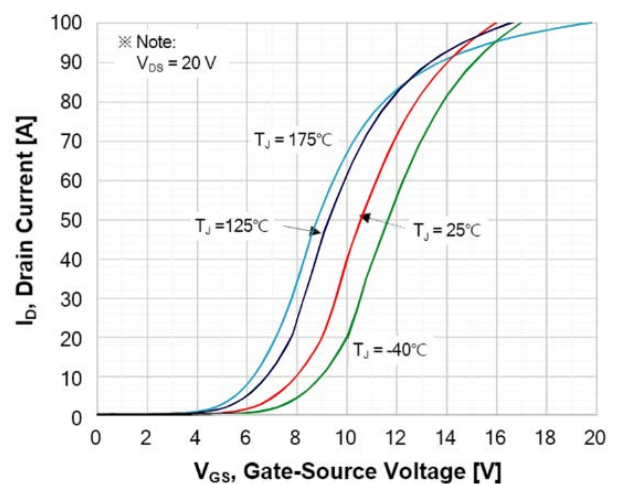


Figure 6. Transfer Characteristics



Typical Performance Characteristics

Figure 7. Diode Forward Voltage Characteristics vs. Source-Drain Current $T_J = -40^\circ\text{C}$

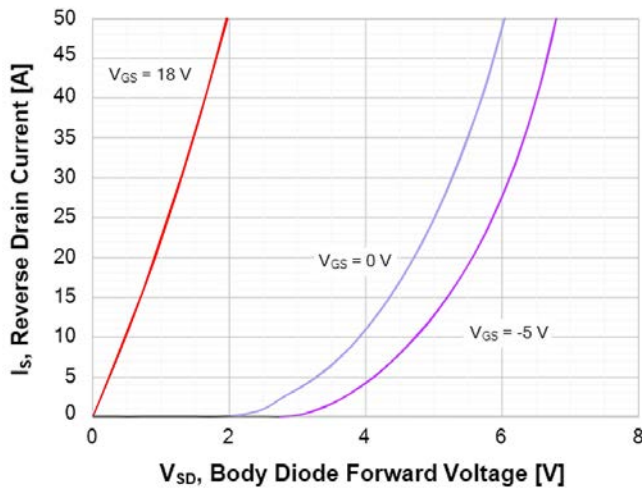


Figure 8. Diode Forward Voltage Characteristics vs. Source-Drain Current $T_J = 25^\circ\text{C}$

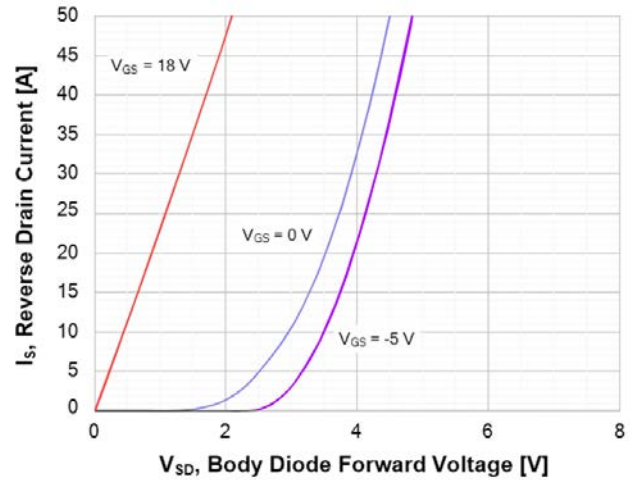


Figure 9. Diode Forward Voltage Characteristics vs. Source-Drain Current $T_J = 125^\circ\text{C}$

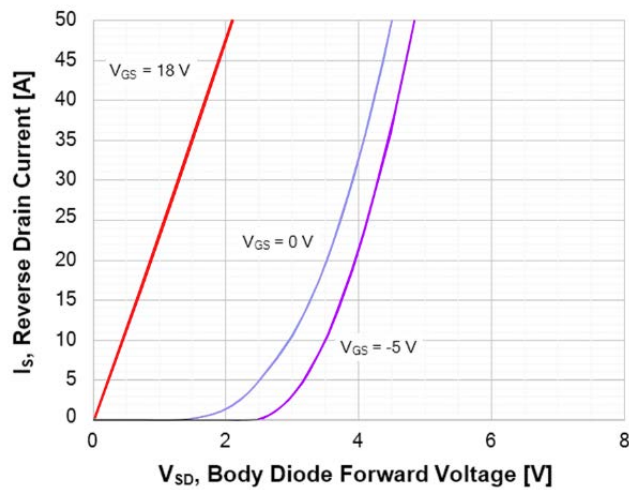


Figure 10. Diode Forward Voltage Characteristics vs. Source-Drain Current $T_J = 175^\circ\text{C}$

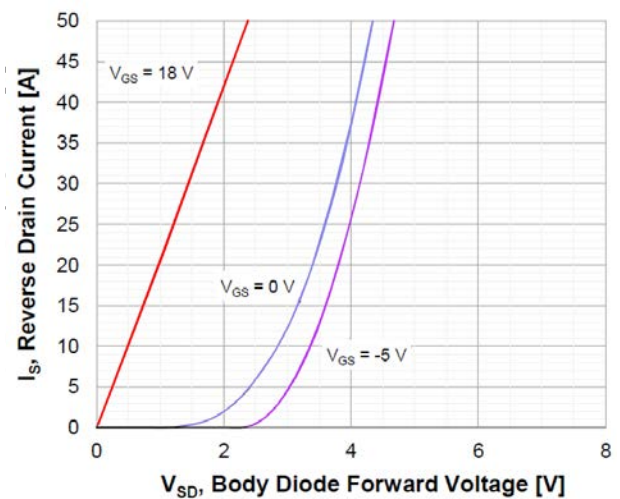


Figure 11. Threshold Voltage vs. Temperature

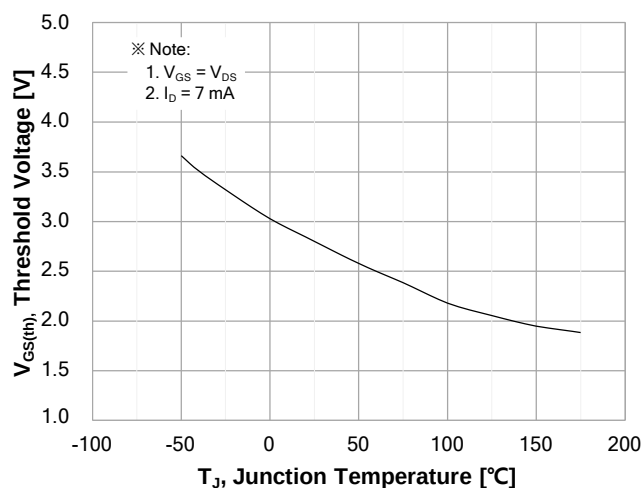
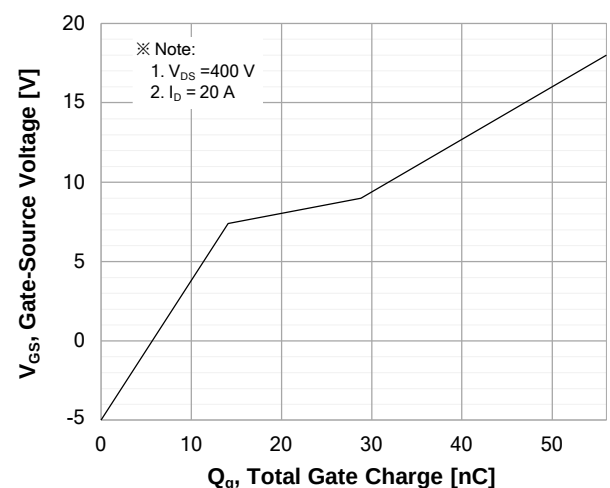


Figure 12. Gate Charge Characteristics



Typical Performance Characteristics

Figure 13. Stored Energy in Output Capacitance

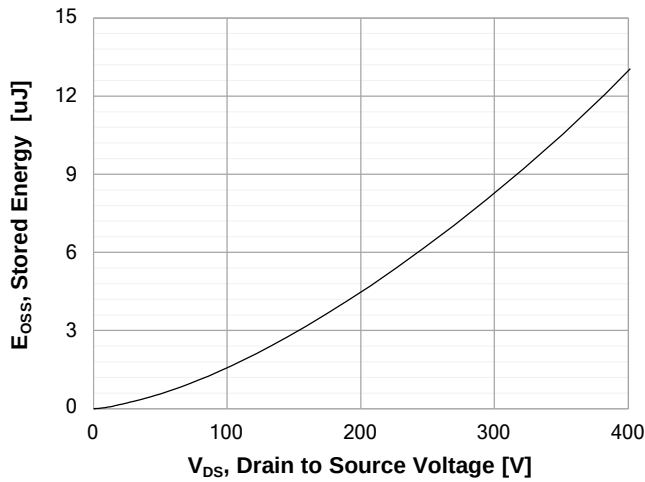


Figure 14. Capacitance Characteristics

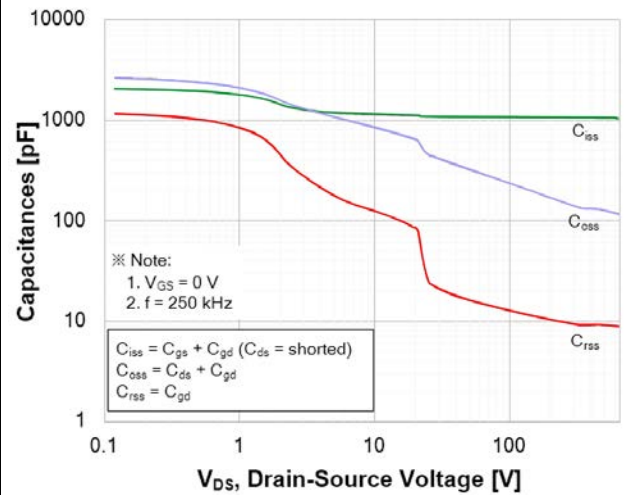


Figure 15. Continuous Drain Current Derating vs. Case Temperature

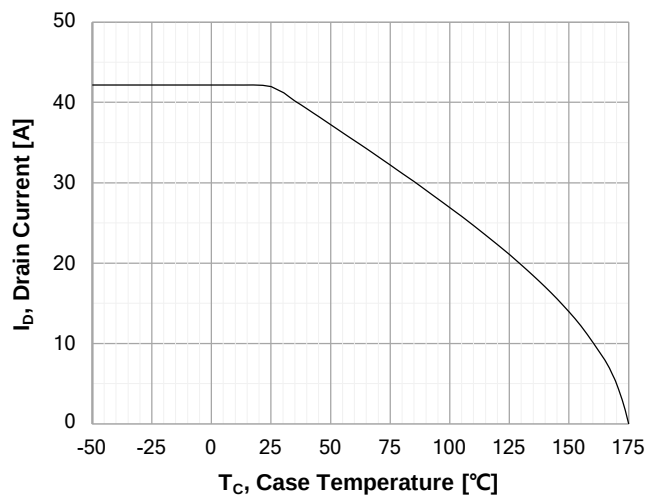


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

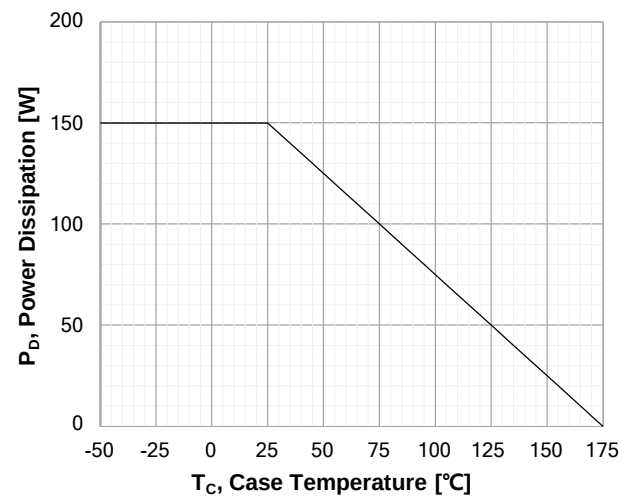


Figure 17. Typ. Switching Losses vs. Drain Current

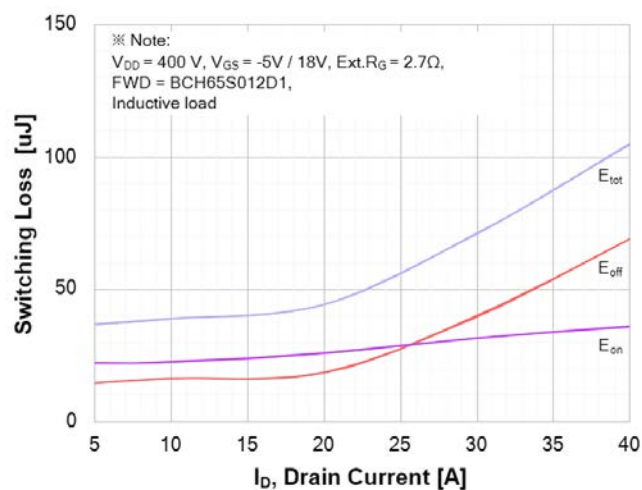
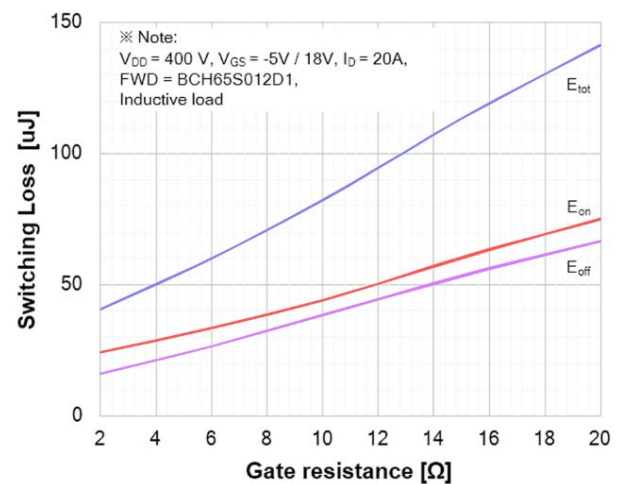


Figure 18. Typ. Switching Losses vs. Gate Resistance



Typical Performance Characteristics

Figure 19. Typ. Switching Losses vs. Drain Current

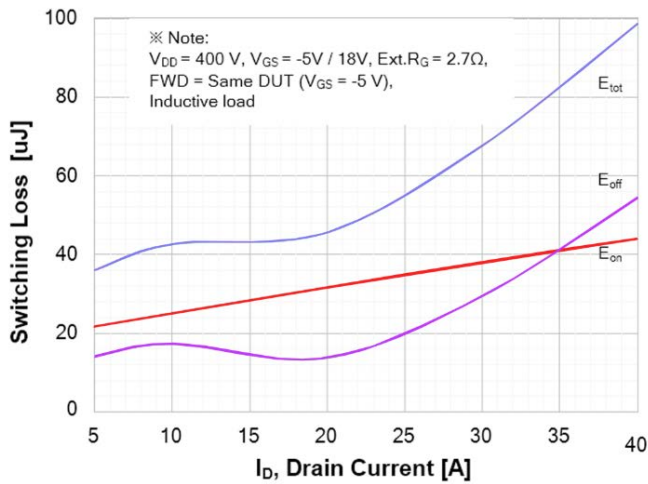


Figure 20. Typ. Switching Losses vs. Gate Resistance

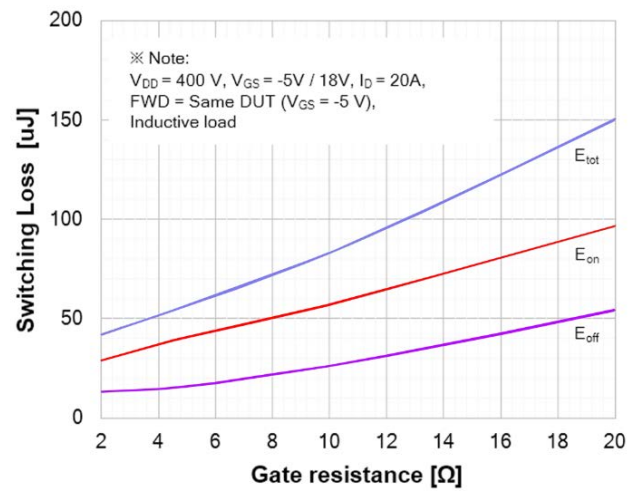


Figure 21. Maximum Safe Operating Area

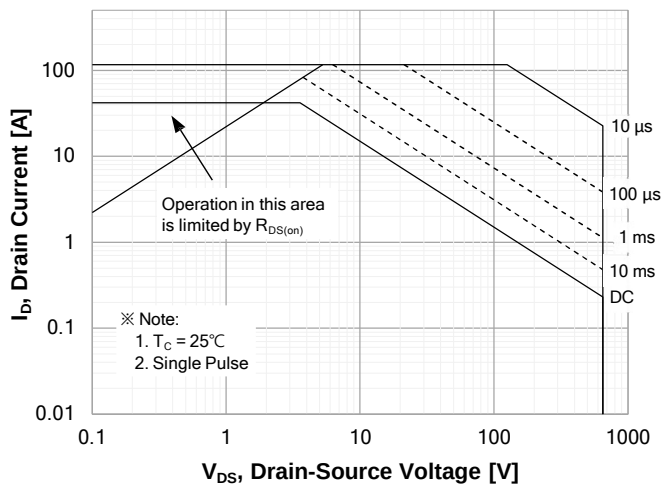
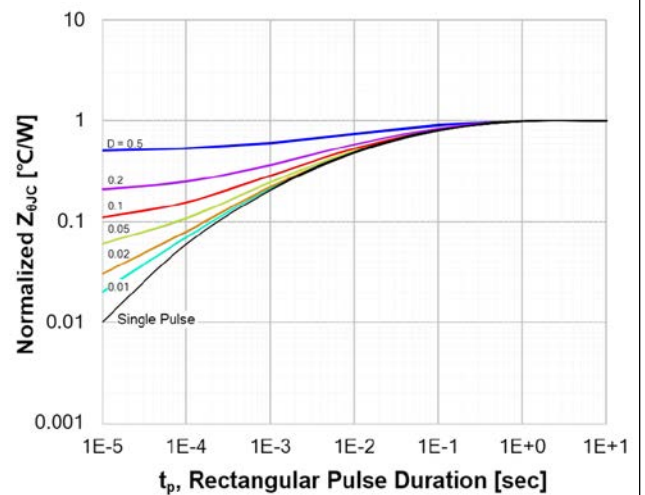


Figure 22. Transient Thermal Response Curve



Typical Performance Characteristics

Figure 21. Inductive Load Switching Test Circuit and Waveforms

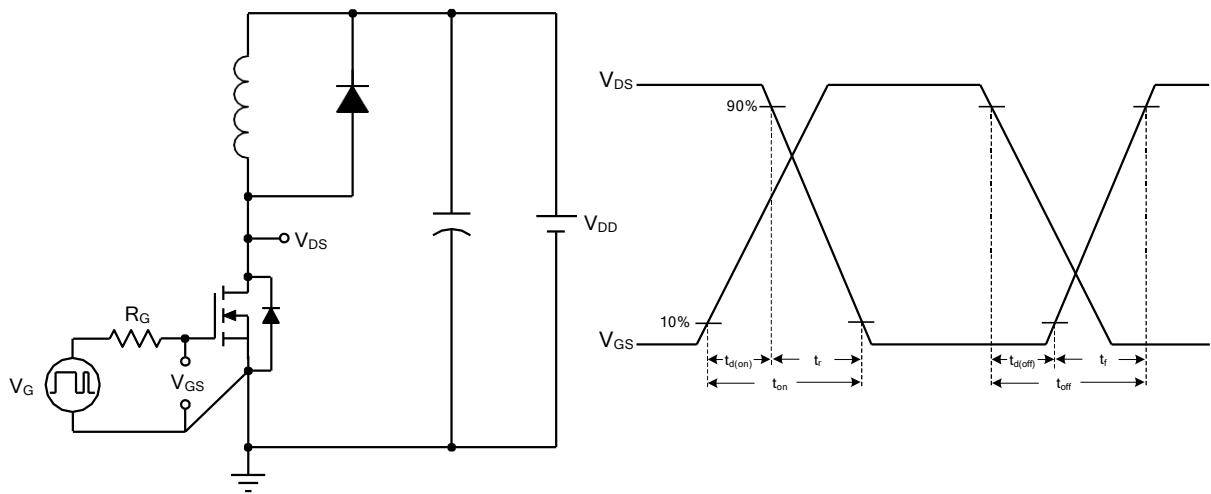
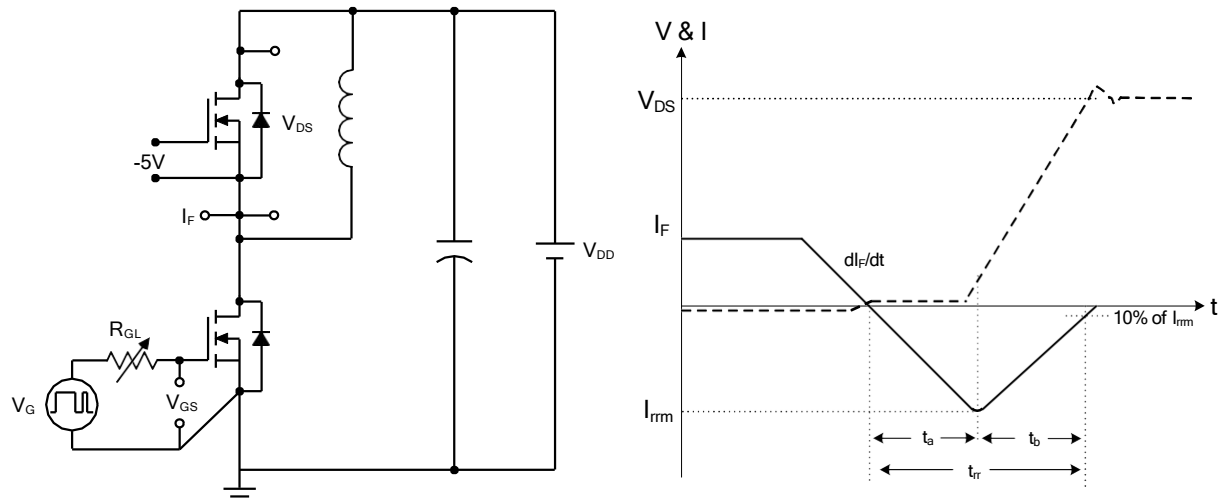
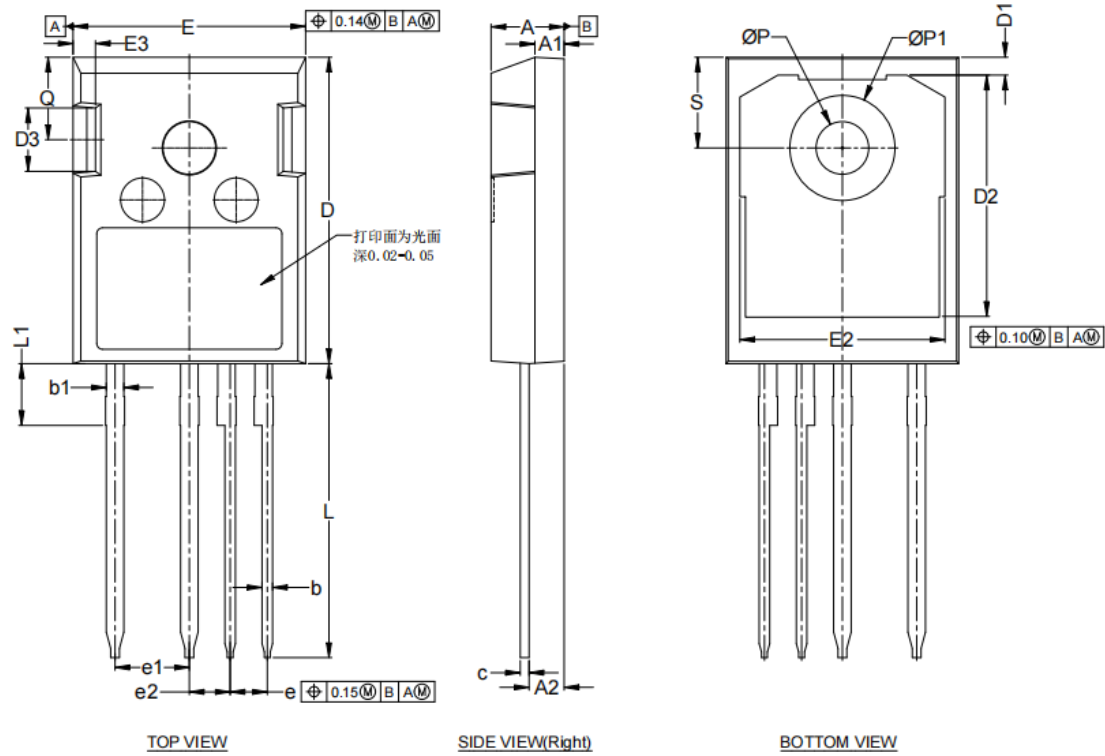


Figure 22. Peak Diode Recovery dv/dt Test Circuit and Waveforms



Package Outlines

TO247-4S



DIM SYMBOL	MIN.	NOM.	MAX.
A	4.900	5.000	5.100
A1	1.940	2.040	2.140
A2	2.300	2.400	2.500
b	0.650	0.720	0.790
b1	1.100	1.200	1.300
c	0.550	0.600	0.700
D	20.850	20.950	21.050
D1	1.022	1.222	1.400
D2	16.348	16.548	16.748
D3	4.232	4.332	4.432
E	15.800	15.900	16.000
E2	13.821	14.021	14.221
E3	1.430	1.530	1.630
e	2.540 BSC.		
e1	5.080 BSC.		
e2	2.790 BSC.		
L	19.900	20.100	20.300
L1	4.024	4.224	4.424
ØP	3.500	3.600	3.700
ØP1	7.088	7.188	7.288
Q	5.435	5.635	5.835
S	6.040	6.200	6.300

* Dimensions in millimeters

Package Marking and Ordering Information

Part Number	Top Marking	Package	Packing Method	Quantity
BCZS65N45M1	BCZS65N45M1	TO-247-4S	Tube	30 units

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